L Number	Hits	Search Text	DB	Time stamp
1	22896	flip near chip	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 11:43
2	10	(flip near chip) and ((chip die) with (core near (area region part portion)) with (peripher$2 near (area region part portion)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 11:51
3	57	(flip near chip) and ((chip die) with (core near (area region part portion)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 12:12
4	7	("5216280" | "5512765" | "5581109" | "5610417" | "5641978" | "6093942" | "6144100").PN.	USPAT	2004/08/20 12:00
5	20	("3894860" | "4792532" | "4860087" | "4978633" | "5066831" | "5153507" | "5239448" | "5258648" | "5281151" | "5341049" | "5381307" | "5391917" | "5422441" | "5490040" | "5510758" | "5523622" | "5545923" | "5672911" | "5686764" | "5703402").PN.	USPAT	2004/08/20 12:05
6	5	("4551746" | "4551747" | "5089881" | "5218230" | "5513076").PN.	USPAT	2004/08/20 12:08
7	1860	((chip die) with (core near (area region part portion)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 12:16
8	6	(((chip die) with (core near (area region part portion)))) and (peripher$2 with (electrostatic near discharge (ESD)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 12:22
9	57	(((chip die) with (core near (area region part portion)))) and ((electrostatic near discharge) ESD)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 12:44
10	6	("5155065" | "5300796" | "5552333" | "5598347" | "5754826" | "6374203").PN.	USPAT	2004/08/20 12:32
11	6	("5155065" | "5300796" | "5552333" | "5598347" | "5754826" | "6374203").PN.	USPAT	2004/08/20 12:33
12	8874	power with ground with (arrang$5 configur$6 layout)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 12:46
13	332	(flip near chip) and (power with ground with (arrang$5 configur$6 layout))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 12:59
14	36	((flip near chip) and (power with ground with (arrang$5 configur$6 layout))) and ESD	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 12:55
15	2	((flip near chip) and (power with ground with (arrang$5 configur$6 layout))) and ((under near ball near metallization) UBM)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 12:54

16	4	(power with ground with (arrang$5 configur$6 layout)) and ((under near ball near metallization) UBM)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 12:55
17	504	(flip near chip) and ((under near ball near metallization) UBM)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 12:55
18	5	((flip near chip) and ((under near ball near metallization) UBM)) and ESD	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 13:00
19	2	((flip near chip) and ((under near ball near metallization) UBM)) and (power with ground with (arrang$5 configur$6 layout))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 12:59
20	492	((flip near chip) and ((under near ball near metallization) UBM)) and bump$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 13:00
21	425	(((flip near chip) and ((under near ball near metallization) UBM)) and bump$1) and connect$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 13:00
22	90	(((flip near chip) and ((under near ball near metallization) UBM)) and bump$1) and (connect$3 near (structure circuit device configur$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/20 13:01